200V N-Channel MOSFET

Lead Free Package and Finish

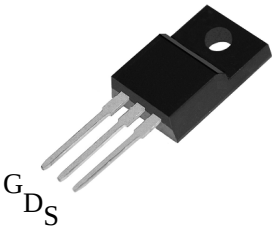
BV_{DSS}	$R_{DS(ON),typ.}$	I_D
200V	22mΩ	90A

General Features

- Proprietary New Planar Technology
- $R_{DS(ON),typ.}$=22mΩ@V_{GS}=10V
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

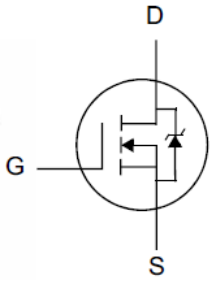
Applications

- DC-DC Converters
- DC-AC Inverters for UPS
- Power Management for Inverter Systems



TO-220F

Package Not to Scale



Ordering Information

Part Number	Package	Brand
PTA27N20N	TO-220F	

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter	PTA27N20N	Unit
V_{DSS}	Drain-to-Source Voltage[1]	200	V
V_{GSS}	Gate-to-Source Voltage	±20	
I_D	Continuous Drain Current	90	A
$I_{D\ @\ Tc\ =100℃}$	Continuous Drain Current @ Tc=100℃	70	
I_{DM}	Pulsed Drain Current at V_{GS}=10V[2]	360	
E_{AS}	Single Pulse Avalanche Energy[5]	784	mJ
dv/dt	Peak Diode Recovery dv/dt[3]	5.0	V/ns
P_D	Power Dissipation	45	W
	Derating Factor above 25℃	0.36	W/℃
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	℃
T_J& T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	PTA27N20N	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.78	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	

Electrical Characteristics

OFF Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	--	--	V	V_{GS}=0V, I_D=250uA
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	uA	V_{DS}=160V, V_{GS}=0V
		--	--	100		V_{DS}=160V, V_{GS}=0V, T_J =125℃
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	V_{GS}=+20V, V_{DS}=0V
		--	--	-100		V_{GS}=-20V, V_{DS}=0V

ON Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance[4]	--	22	27	mΩ	V_{GS}=10V, I_D=45A
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	3.0	4.0	V	V_{DS}=V_{GS}, I_D=250uA

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	5871	--	pF	V_{GS}=0V, V_{DS}=25V, f=1.0MHz
C_{rss}	Reverse Transfer Capacitance	--	165	--		
C_{oss}	Output Capacitance	--	392	--		
Q_g	Total Gate Charge	--	130	--	nC	V_{DD}=160V, I_D=45A, V_{GS}=0 to 10V
Q_{gs}	Gate-to-Source Charge	--	22	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	38	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	29	--	ns	V_{DD}=100V, I_D=45A, V_{GS}= 10V R_G=4.0 Ω
t_{rise}	Rise Time	--	45	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	22	--		
t_{fall}	Fall Time	--	41	--		

Source-Drain Body Diode Characteristics

T_J=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current[4]	--	--	90	A	Integral PN-diode in MOSFET
I_{SM}	Pulsed Source Current[4]	--	--	360		
V_{SD}	Diode Forward Voltage	--	--	1.1	V	I_S=56A, V_{GS}=0V
trr	Reverse recovery time	--	80	--	ns	V_{GS}=0V ,I_F=45A, di_F/dt=100A/μs
Qrr	Reverse recovery charge	--	160	--	nC	

Note:

[1] T_J=+25℃ to +150℃
[2] Repetitive rating; pulse width limited by maximum junction temperature.
[3] I_{SD}= 20A di/dt < 100 A/μs, V_{DD} < BV_{DSS}, T_J=+150℃.
[4] Pulse width≤380μs; duty cycle≤2%.
[5] L=0.5mH

Typical Characteristics

Figure 1: Power Dissipation

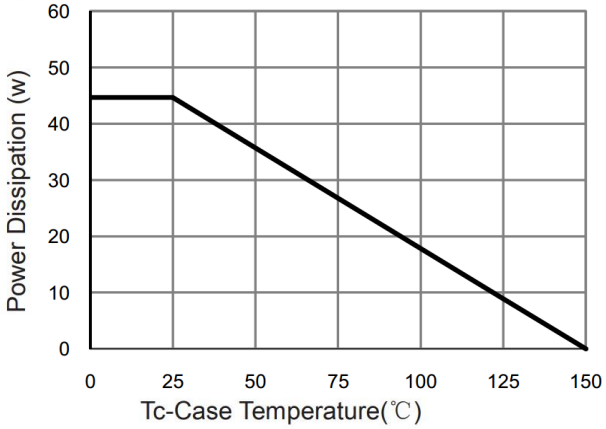


Figure 2: Drain Current

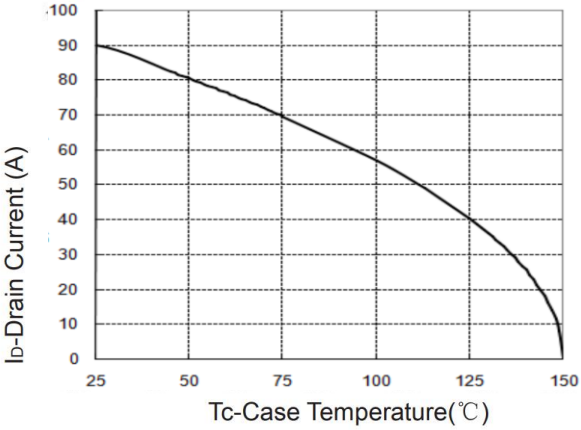


Figure 3: Safe Operation Area

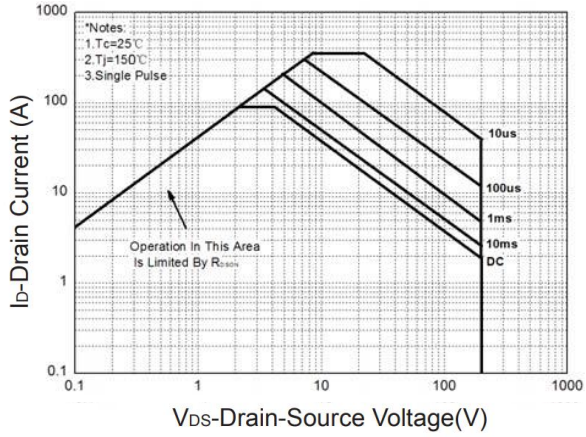


Figure 4: Thermal Transient Impedance

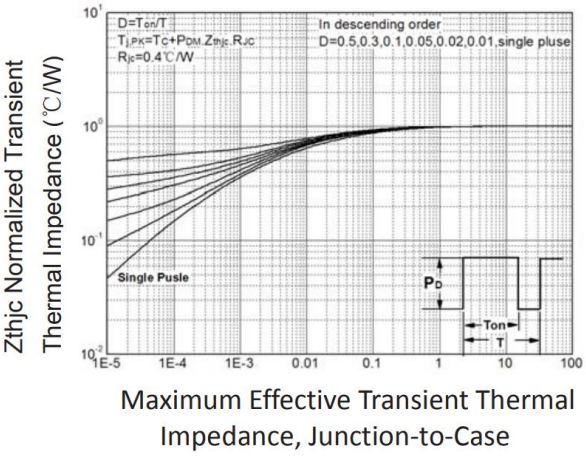


Figure 5: Output Characteristics

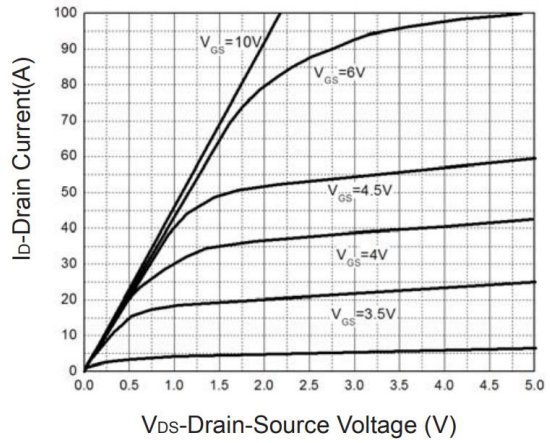


Figure 6: Drain-Source On Resistance

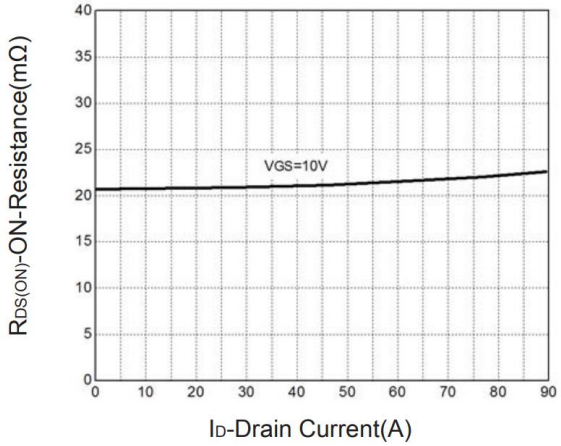


Figure 7: Gate-Source Vs. On-Resistance

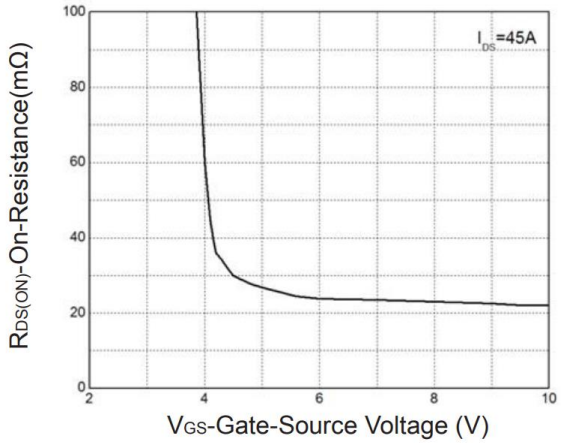


Figure 8: Gate-Source Forward

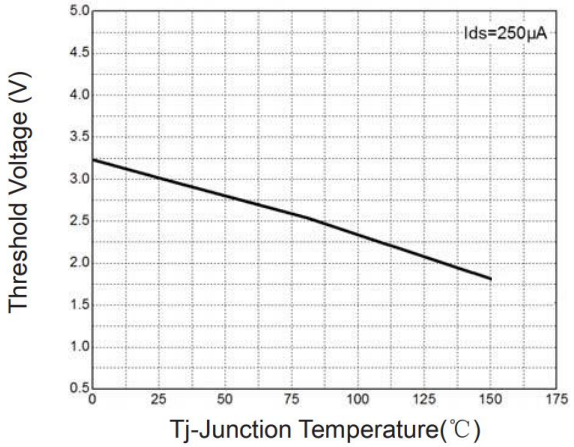
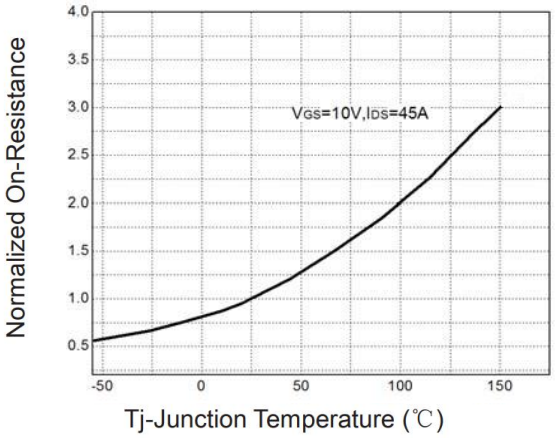


Figure 9: On-Resistance vs. Temperature

Figure 10: Source-Drain Diode Forward



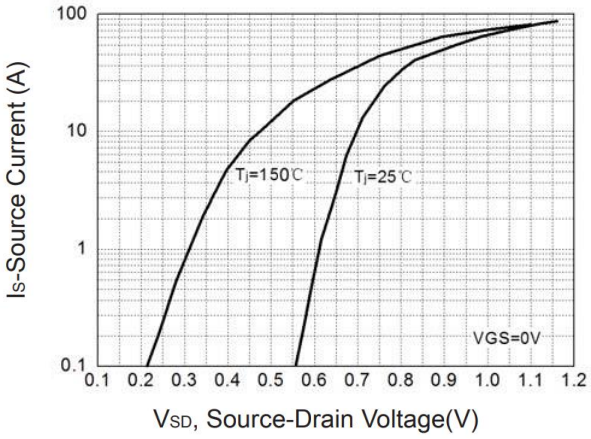
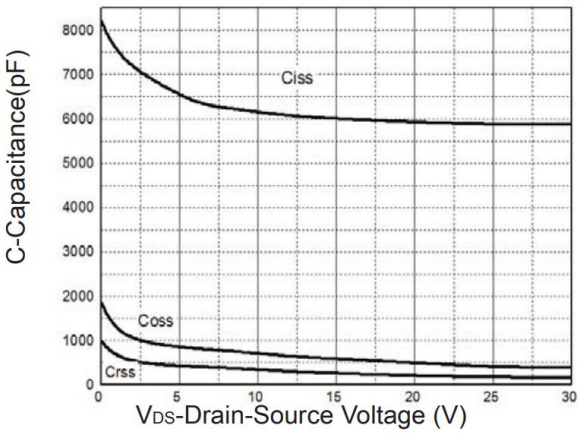
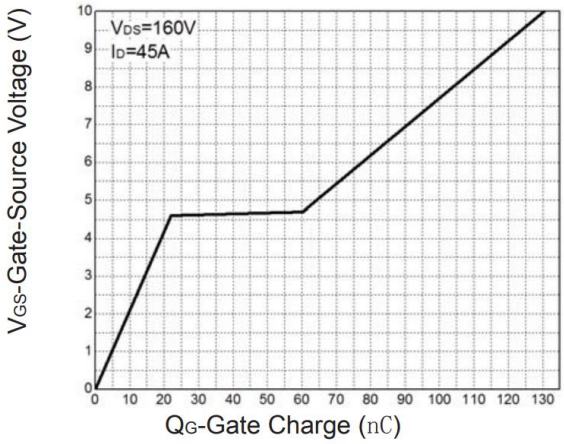


Figure 11: Capacitance Characteristics

Figure 12: Gate Charge Characteristics





Test Circuits and Waveforms

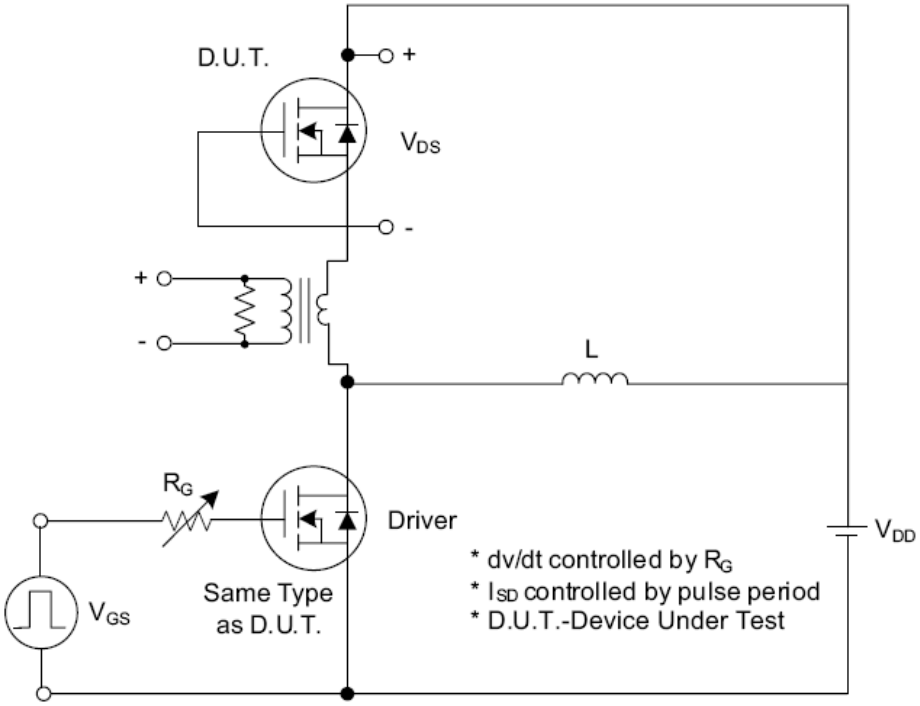


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

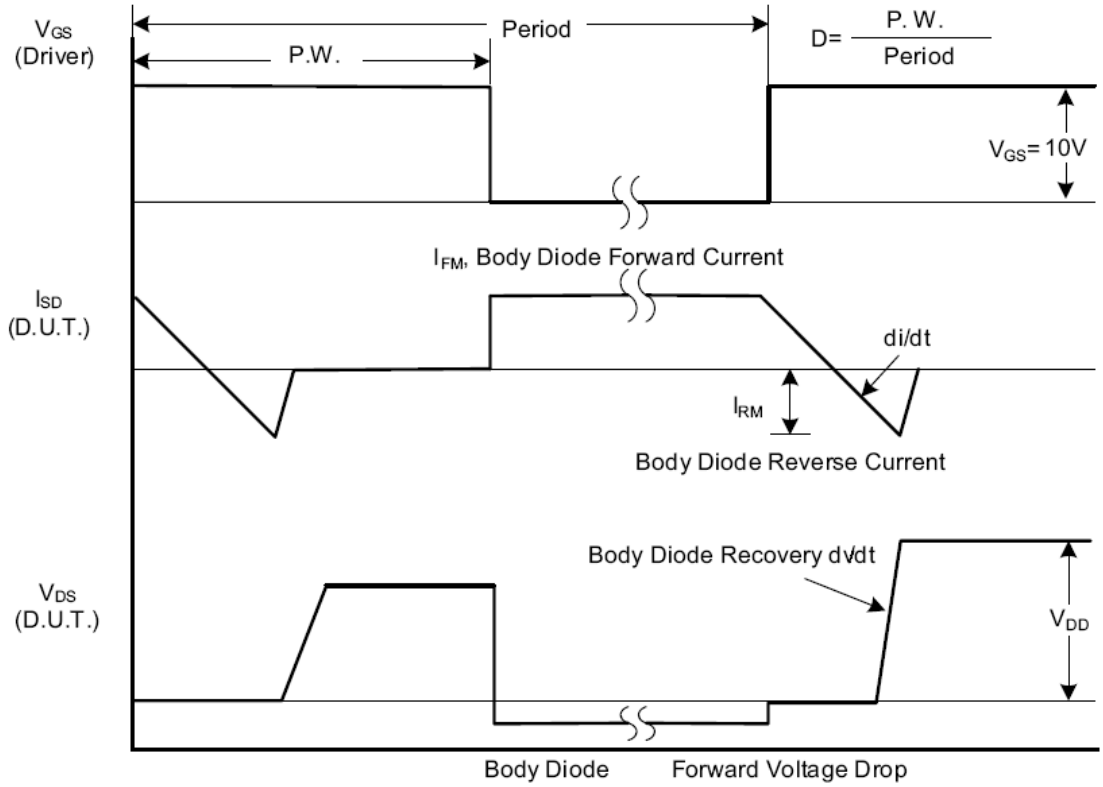


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

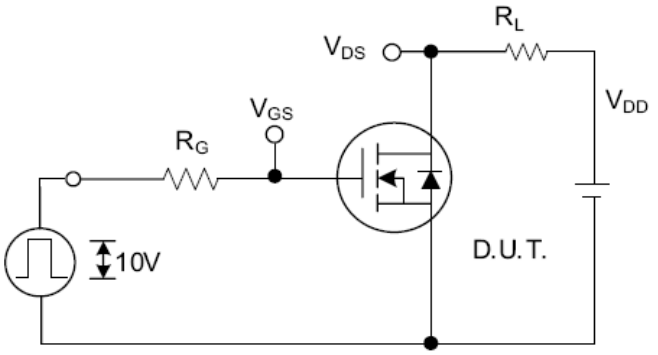


Fig. 2.1 Switching Test Circuit

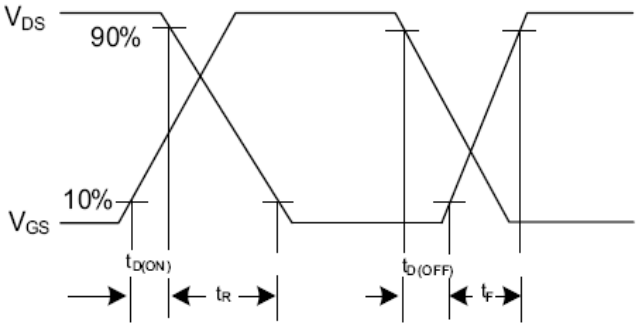


Fig. 2.2 Switching Waveforms

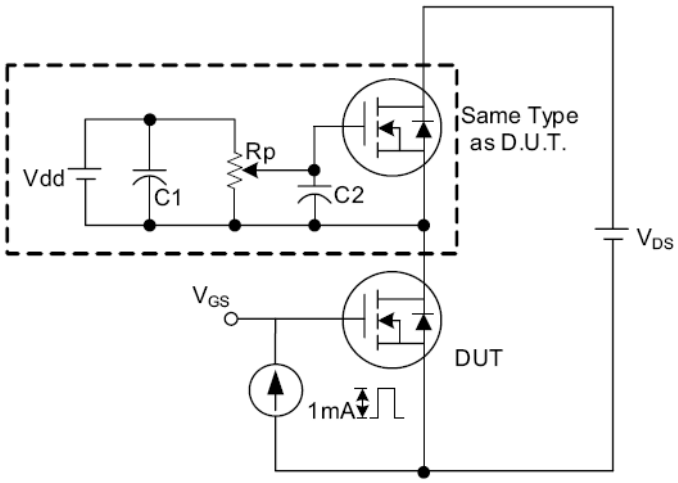


Fig. 3 . 1 Gate Charge Test Circuit

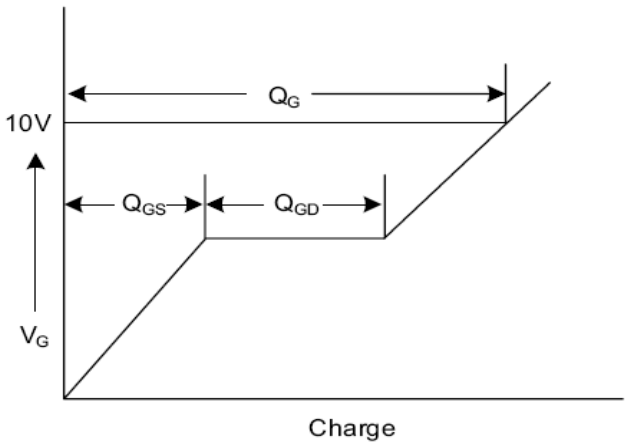


Fig. 3 . 2 Gate Charge Waveform

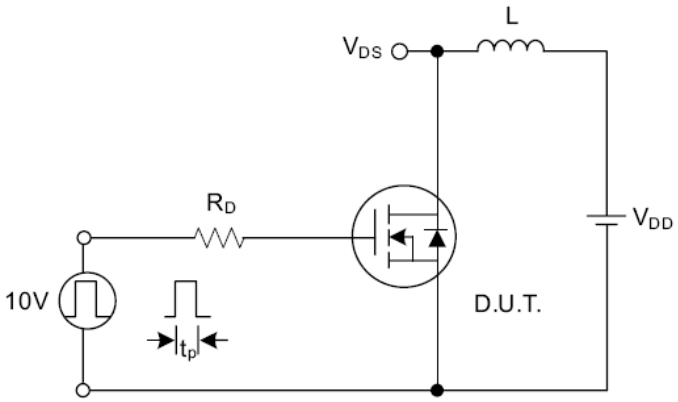


Fig. 4.1 Unclamped Inductive Switching Test Circuit

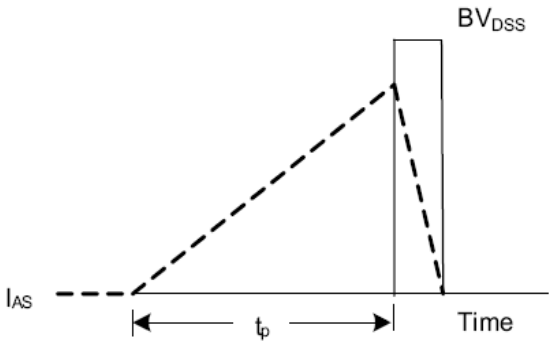


Fig. 4.2 Unclamped Inductive Switching Waveforms

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